IN THE CLAIMS

This listing of claims replaces all prior claim listings:

- 1. (Cancelled)
- 2. (Currently Amended) A solid state imaging device with a unit pixel having:
- a photoelectric converter for generating a charge in accordance with an amount of incident light[[,]];
- a transfer transistor for transferring a signal of the photoelectric converter to a floating node[[,]];

an amplifier transistor for outputting a signal of the floating node to a signal line,

- a reset transistor for resetting the floating node, at least one of a plurality of potentials supplied to a gate electrode of the reset transistor being a negative potential[[,]]; and
- a portion able to supply three or more types of potentials to the gate electrode of the reset transistor,

wherein,

the device has a portion able to set the gate potential when bringing the reset transistor from an On state to an OFF state at a negative power source potential after passing a ground level power source potential from a positive high level power source potential.

- 3. 4. (Cancelled)
- 5. (Currently Amended) A solid state imaging device as set forth in claim [[3]] 2, wherein at both timings of sampling and holding a precharge phase and a data phase, the gate potential of the reset transistor is set at the ground potential.
- 6. (Original) A solid state imaging device as set forth in claim 5, wherein in a period during which the gate potential of the reset transistor of the selected pixel is set at the ground potential, the gate potential of the reset transistor of the nonselected pixel is a negative potential.

7. - 8. (Cancelled)

9. (Currently Amended) A camera system having:

a solid state imaging device with a unit pixel having a photoelectric converter for generating a charge in accordance with an amount of incident light,

a transfer transistor for transferring a signal of the photoelectric converter to a floating node,

an amplifier transistor for outputting a signal of the floating node to a signal line,

a reset transistor for resetting the floating node, at least one of a plurality of potentials supplied to a gate electrode of the reset transistor being a negative potential[[,]]; and

a portion able to supply three or more types of potentials to the gate electrode of the reset transistor;

an optical system for guiding an incident light to an imaging portion of the solid state imaging device; and

a signal processing circuit for processing an output signal of the solid state imaging device,

wherein,

the device has a portion able to set the gate potential when bringing the reset transistor from an On state to an OFF state at a negative power source potential after passing a ground level power source potential from a positive high level power source potential.